



ELECTRONICS, INC.
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NTE575 General Purpose Silicon Rectifier Fast Recovery

Features:

- Low Switching Noise
- Low Forward Voltage Drop
- Low Thermal Resistance
- High Current Capability
- High Switching Capability
- High Surge Capability
- High Reliability

Maximum Ratings and Electrical Characteristics:

($T_A = +25^\circ\text{C}$ unless otherwise specified. Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%)

Maximum Recurrent Peak Reverse Voltage, V_{RRM}	1000V
Maximum RMS Voltage, V_{RMS}	700V
Maximum DC Blocking Voltage, V_{DC}	1000V
Maximum Average Forward Rectified Output Current ($T_A = +55^\circ\text{C}$), $I_{(AV)}$	1A
Peak Forward Surge Current, I_{FSM} (8.3ms single half sine wave superimposed on rated load)	35A
Maximum Instantaneous Forward Voltage (At 1A), V_F	1.5V
Maximum DC Reverse Current ($V_{DC} = 1000\text{V}$), I_R	50 μA
Maximum Reverse Recovery Time ($I_F = 0.5\text{A}$, $I_R = 1\text{A}$, $I_{RR} = 0.25\text{A}$), t_{rr}	70ns
Typical Junction Capacitance (Note 1), C_J	15pF
Thermal Resistance, Junction-to-Air ($^{\circ}\text{W}/\text{fin}$), R_{thJA}	50 $^{\circ}\text{C}/\text{W}$
Operating Junction Temperature Range, T_J	-65 $^{\circ}$ to +150 $^{\circ}\text{C}$
Storage Temperature Range, T_{stg}	-65 $^{\circ}$ to +150 $^{\circ}\text{C}$

Note 1. Measured at 1MHz and applied reverse voltage of 4V.

